



**MMBT2222AT** Transistor(NPN)

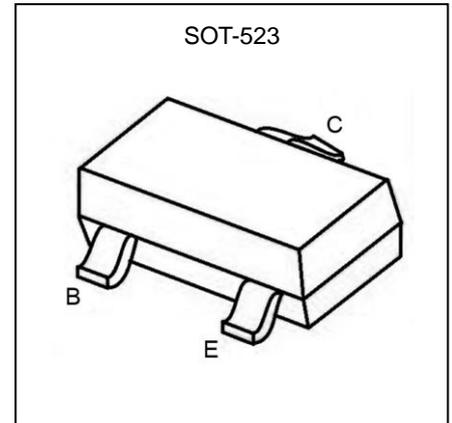
**Features**

- Epitaxial planar die construction

**Marking: 1P**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

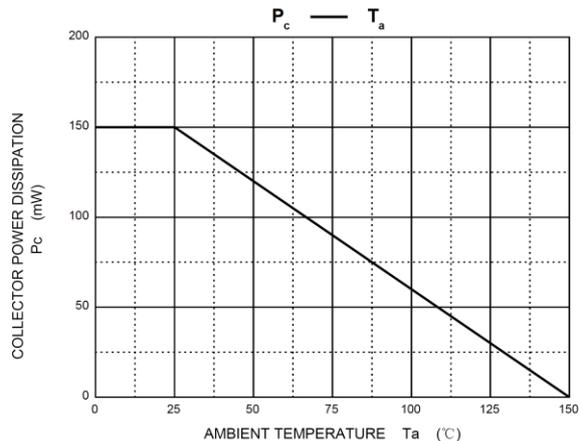
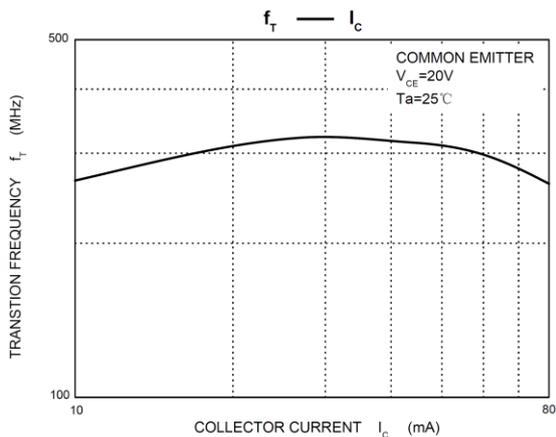
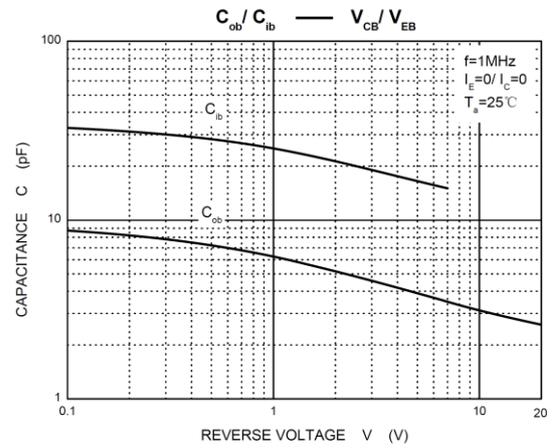
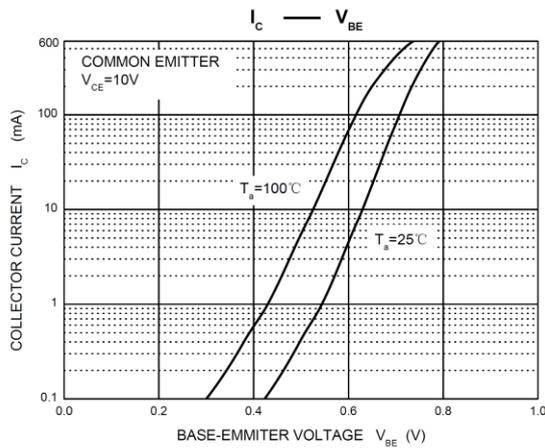
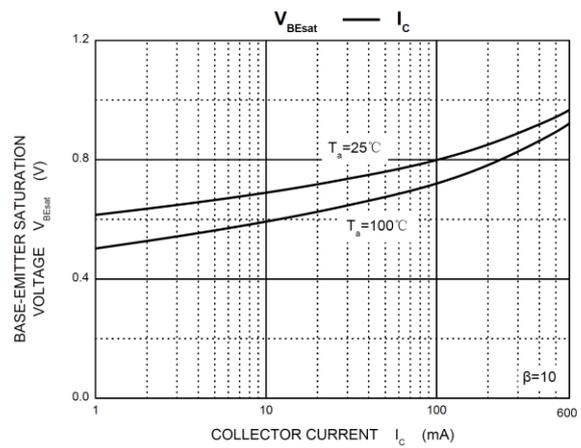
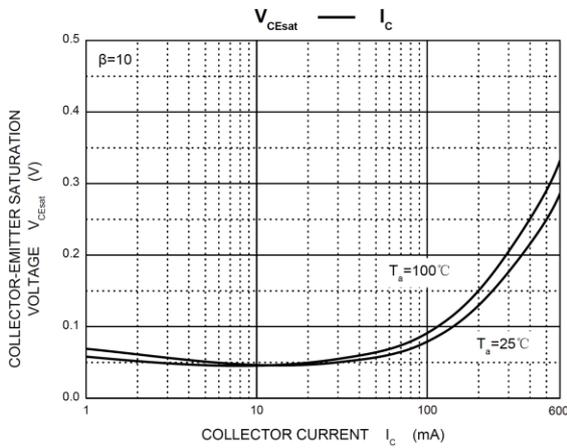
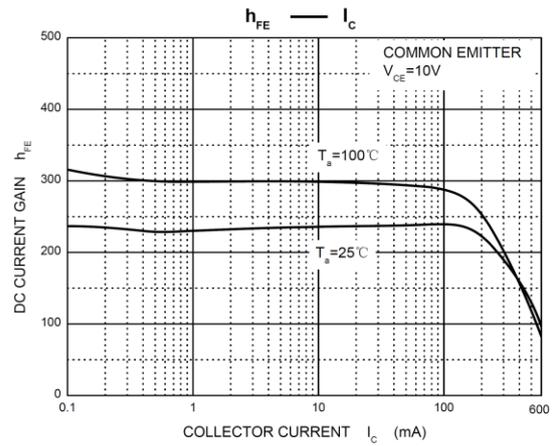
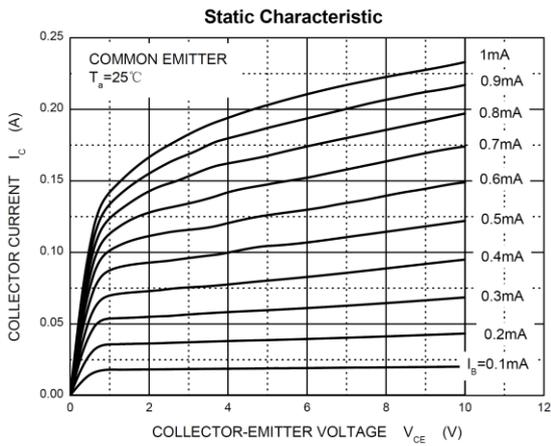
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	75	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current -Continuous	I <sub>c</sub>	0.5	A
Power Dissipation	P <sub>d</sub>	0.15	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C



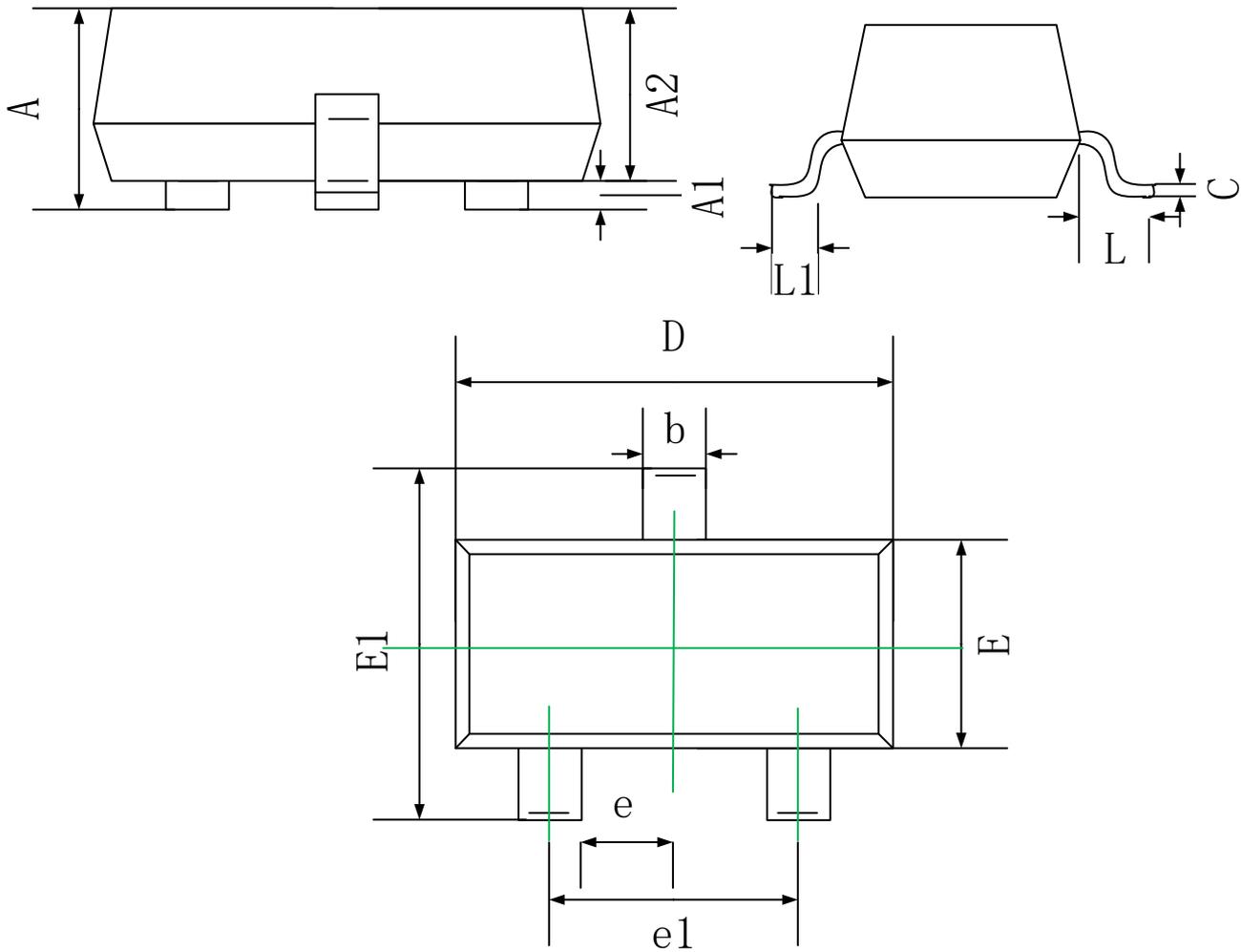
**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> =10μA, I <sub>E</sub> =0	75		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> =10mA, I <sub>B</sub> =0	40		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>c</sub> =0	6		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0		10	nA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =60V, V <sub>EB(off)</sub> =3V		10	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =3V, I <sub>c</sub> =0		10	nA
DC current gain	h <sub>FE1</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> =0.1mA	40		
	h <sub>FE2</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> =150mA	100	300	
	h <sub>FE3</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> =500mA	42		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =150mA, I <sub>B</sub> =15mA		0.3	V
		I <sub>c</sub> =500mA, I <sub>B</sub> =50mA		1	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =150mA, I <sub>B</sub> =15mA		1.2	V
		I <sub>c</sub> =500mA, I <sub>B</sub> =50mA		2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>c</sub> =20mA, f=100MHz	300		MHZ
Delay Time	t <sub>d</sub>	V <sub>CC</sub> =30V, I <sub>c</sub> =150mA,		10	ns
Rise Time	t <sub>r</sub>	V <sub>BE(off)</sub> =-0.5V, I <sub>B1</sub> =15mA		25	ns
Storage Time	t <sub>s</sub>	V <sub>CC</sub> =30V, I <sub>c</sub> =150mA,		225	ns
Fall Time	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> =15mA		60	ns

**Typical Characteristics**



## SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.55 REF	
$\theta$	0°	8°